





100V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

Features

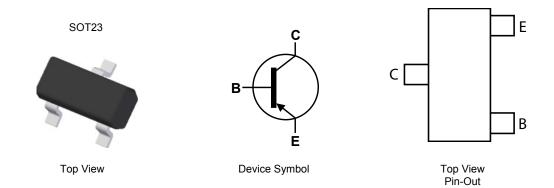
- BV_{CEO} > -100V
- I_C = -1A Continuous Collector Current
- I_{CM} = -2.5A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -330mV @ -1A
- $R_{CE(SAT)} = 210 \text{m}\Omega$ for a low equivalent on-resistance
- 625mW power dissipation
- h_{FE} characterised up to -1.5A for high current gain hold-up
- Complementary NPN Type: FMMT624
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- · Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight 0.008 grams (approximate)

Applications

- High-side driver
- Load disconnect switch
- Motor drive



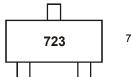
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT723TA	723	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

Marking Information



723 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2.5	Α
Base Current	I _B	-500	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	625	mW
Power Dissipation (Note 6)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R ₀ JL	194	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

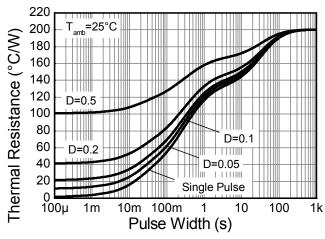
Notes:

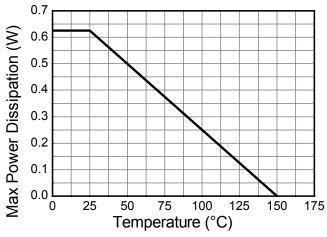
- 5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note 5, except the device is measured at $t \le 5$ sec.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



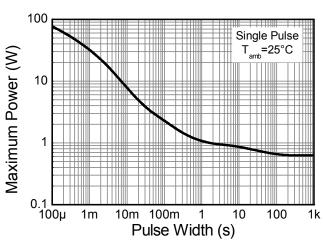


Thermal Characteristics and Derating information

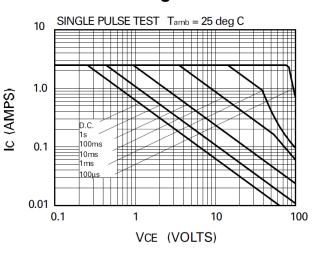




Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation

Safe Operating Area





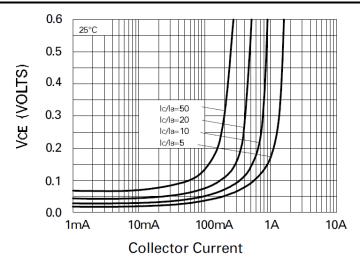
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

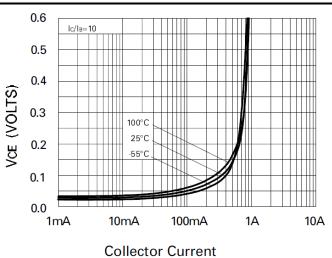
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-200	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-100	-160	-	V	$I_C = -10 \text{mA}$
Emitter-Base Breakdown Voltage	BV_EBO	-7	-8.8	-	V	$I_{E} = -100 \mu A$
Collector Cutoff Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -80V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	$V_{EB} = -5.6V$
Collector Emitter Cutoff Current	I _{CES}	-	<1	-100	nA	V _{CE} = -80V
		300	475	-		$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		300	450	-		$I_C = -0.1A$, $V_{CE} = -10V$
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	250	375	-	-	$I_C = -0.5A$, $V_{CE} = -10V$
		-	250	-		$I_C = -1A$, $V_{CE} = -10V$
		-	30	-		I _C = -1.5A, V _{CE} = -10V
		-	-50	-80		$I_C = -0.1A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	-	-125	-200	mV	$I_C = -0.5A$, $I_B = -50mA$
		-	-210	-330		$I_C = -1A$, $I_B = -150mA$
Base-Emitter Turn-On Voltage(Note 9)	$V_{BE(on)}$	-	-0.71	-1.0	V	$I_C = -1A$, $V_{CE} = -10V$
Base-Emitter Saturation Voltage(Note 9)	V _{BE(sat)}	-	-0.89	-1.0	V	$I_C = -1A$, $I_B = -150mA$
Output Capacitance	C_{obo}	-	13	20	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f⊤	150	200	-	MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$
Turn-On Time	t _{on}	-	50	-	ns	$V_{CC} = -50V, I_{C} = -0.5A$
Turn-Off Time	t _{off}	-	760	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

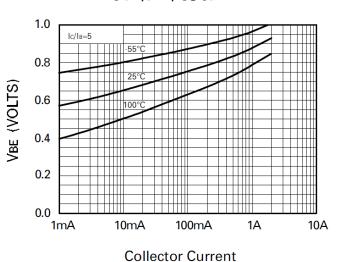




VCE(SAT) vs IC

1.4 Vce=10V 1.2 Dypical Gain (hE) Normalised Gain 1.0 8.0 0.6 0.4 0.2 0.0 100mA 10mA 1A 1mA 10A

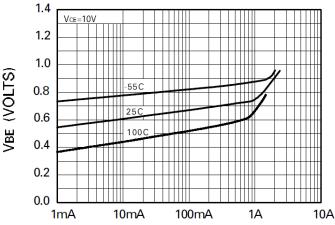
VCE(SAT) vs IC



VBE(SAT) vs IC

Collector Current

hfe vs IC



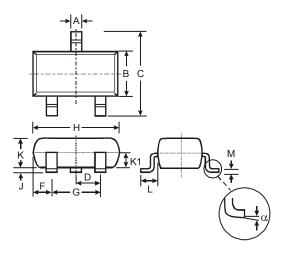
Collector Current

VBE(ON) vs IC



Package Outline Dimensions

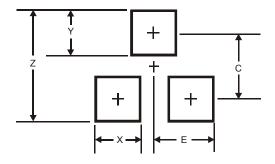
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Y	0.9		
С	2.0		
Ш	1.35		





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